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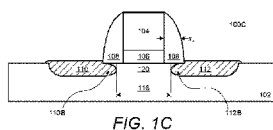
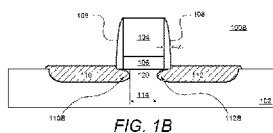
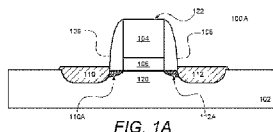
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(54) Title: TRANSISTORS WITH HIGH CONCENTRATION OF BORON DOPED GERMANIUM



(57) Abstract: Techniques are disclosed for forming transistor devices having source and drain regions with high concentrations of boron doped germanium. In some embodiments, an in situ boron doped germanium, or alternatively, boron doped silicon germanium capped with a heavily boron doped germanium layer, are provided using selective epitaxial deposition in the source and drain regions and their corresponding tip regions. In some such cases, germanium concentration can be, for example, in excess of 50 atomic % and up to 100 atomic %, and the boron concentration can be, for instance, in excess of $1 \times 10^{20} \text{ cm}^{-3}$. A buffer providing graded germanium and/or boron concentrations can be used to better interface disparate layers. The concentration of boron doped in the germanium at the epi-metal interface effectively lowers parasitic resistance without degrading tip abruptness. The techniques can be embodied, for instance, in planar or non-planar transistor devices.





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